

NPN - MPS650, MPS651; PNP - MPS750, MPS751

MPS651 and MPS751 are Preferred Devices

Amplifier Transistors

Features

- Pb-Free Packages are Available*

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage MPS650; MPS750 MPS651; MPS751	V_{CE}	40 60	Vdc
Collector-Base Voltage MPS650; MPS750 MPS651; MPS751	V_{CB}	60 80	Vdc
Emitter-Base Voltage	V_{EB}	5.0	Vdc
Collector Current - Continuous	I_C	2.0	Adc
Total Power Dissipation @ $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D	625 5.0	mW mW/ $^\circ\text{C}$
Total Power Dissipation @ $T_C = 25^\circ\text{C}$ Derate above 25°C	P_D	1.5 12	W mW/ $^\circ\text{C}$
Operating and Storage Junction Temperature Range	T_J, T_{stg}	-55 to +150	$^\circ\text{C}$

THERMAL CHARACTERISTICS

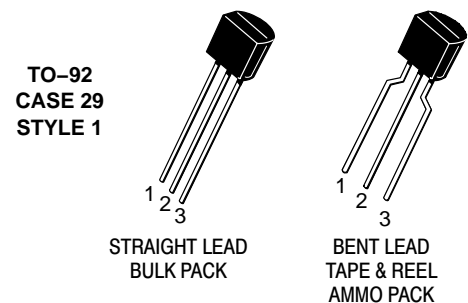
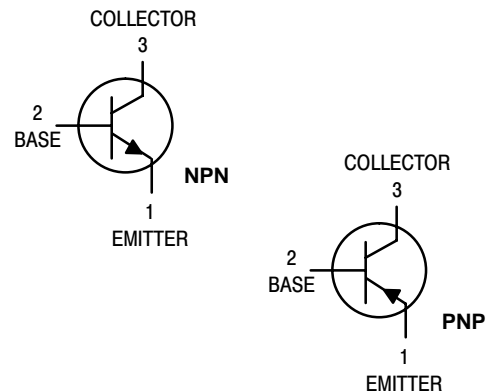
Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction-to-Ambient	V_{CE}	200	$^\circ\text{C}/\text{W}$
Thermal Resistance, Junction-to-Case	V_{CB}	83.3	$^\circ\text{C}/\text{W}$

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

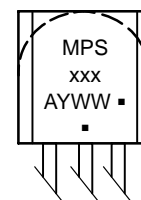
*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.



ON Semiconductor®



MARKING DIAGRAM



xxx = 650, 750, 651, or 751
A = Assembly Location
Y = Year
WW = Work Week
■ = Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 4 of this data sheet.

Preferred devices are recommended choices for future use and best overall value.

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ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit	
OFF CHARACTERISTICS					
Collector–Emitter Breakdown Voltage (Note 1) (I _C = 10 mA, I _B = 0)	MPS650, MPS750 MPS651, MPS751	V _{(BR)CEO}	40 60	– –	Vdc
Collector–Base Breakdown Voltage (I _C = 100 μA, I _E = 0)	MPS650, MPS750 MPS651, MPS751	V _{(BR)CBO}	60 80	– –	Vdc
Emitter–Base Breakdown Voltage (I _C = 0, I _E = 10 μA)		V _{(BR)EBO}	5.0	–	Vdc
Collector Cutoff Current (V _{CB} = 60 Vdc, I _E = 0) (V _{CB} = 80 Vdc, I _E = 0)	MPS650, MPS750 MPS651, MPS751	I _{CBO}	– –	0.1 0.1	μA
Emitter Cutoff Current (V _{EB} = 4.0 V, I _C = 0)		I _{EBO}	–	0.1	μA

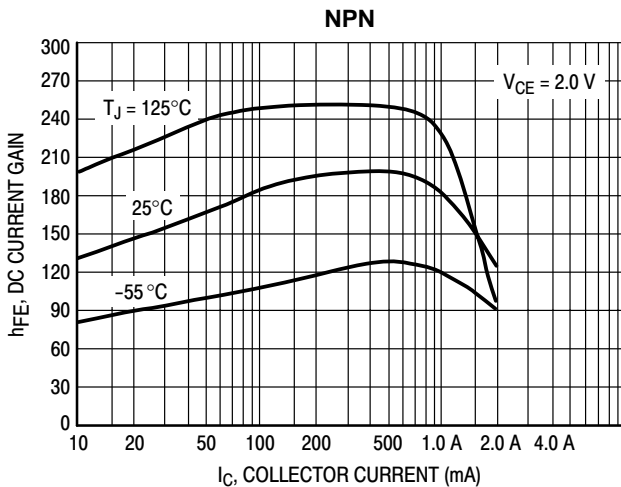
ON CHARACTERISTICS (Note 1)

DC Current Gain (I _C = 50 mA, V _{CE} = 2.0 V) (I _C = 500 mA, V _{CE} = 2.0 V) (I _C = 1.0 A, V _{CE} = 2.0 V) (I _C = 2.0 A, V _{CE} = 2.0 V)		h _{FE}	75 75 75 40	– – – –	–
Collector–Emitter Saturation Voltage (I _C = 2.0 A, I _B = 200 mA) (I _C = 1.0 A, I _B = 100 mA)		V _{CE(sat)}	– –	0.5 0.3	Vdc
Base–Emitter On Voltage (I _C = 1.0 A, V _{CE} = 2.0 V)		V _{BE(on)}	–	1.0	Vdc
Base–Emitter Saturation Voltage (I _C = 1.0 A, I _B = 100 mA)		V _{BE(sat)}	–	1.2	Vdc

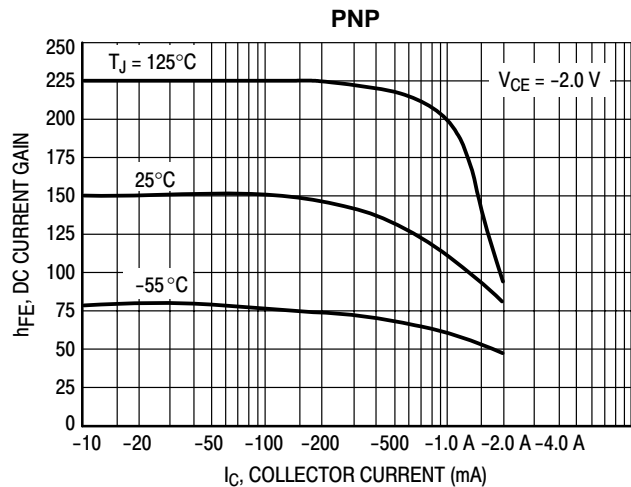
SMALL-SIGNAL CHARACTERISTICS

Current–Gain – Bandwidth Product (Note 2) (I _C = 50 mA, V _{CE} = 5.0 Vdc, f = 100 MHz)		f _T	75	–	MHz
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1. Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle = 2.0%.
2. f_T is defined as the frequency at which |h_{fe}| extrapolates to unity.



**Figure 1. MPS650, MPS651
Typical DC Current Gain**



**Figure 2. MPS750, MPS751
Typical DC Current Gain**

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ORDERING INFORMATION

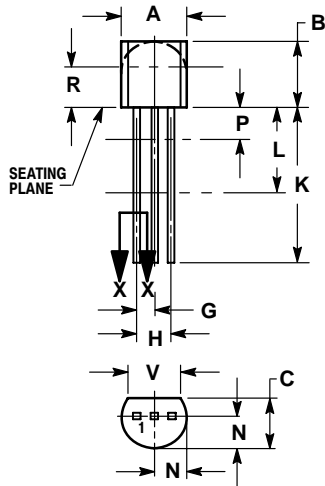
Device	Package	Shipping†
MPS650	TO-92	5000 Units / Bulk
MPS650G	TO-92 (Pb-Free)	5000 Units / Bulk
MPS650RLRAG	TO-92 (Pb-Free)	2000 / Tape & Reel
MPS650ZL1G	TO-92 (Pb-Free)	2000 / Tape & Ammunition
MPS651	TO-92	5000 Units / Bulk
MPS651G	TO-92 (Pb-Free)	5000 Units / Bulk
MPS651RLRAG	TO-92 (Pb-Free)	2000 / Tape & Reel
MPS651RLRM	TO-92	2000 / Tape & Ammunition
MPS651RLRMG	TO-92 (Pb-Free)	2000 / Tape & Ammunition
MPS750G	TO-92 (Pb-Free)	5000 Units / Bulk
MPS750RLRAG	TO-92 (Pb-Free)	2000 / Tape & Reel
MPS750RLRP	TO-92	2000 / Tape & Ammunition
MPS750RLRPG	TO-92 (Pb-Free)	2000 / Tape & Ammunition
MPS751	TO-92	5000 Units / Bulk
MPS751G	TO-92 (Pb-Free)	5000 Units / Bulk
MPS751RLRA	TO-92	2000 / Tape & Reel
MPS751RLRAG	TO-92 (Pb-Free)	2000 / Tape & Reel
MPS751RLRP	TO-92	2000 / Tape & Ammunition
MPS751RLRPG	TO-92 (Pb-Free)	2000 / Tape & Ammunition
MPS751ZL1G	TO-92 (Pb-Free)	2000 / Tape & Ammunition

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

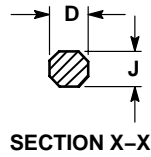
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PACKAGE DIMENSIONS

TO-92 (TO-226)
CASE 29-11
ISSUE AM



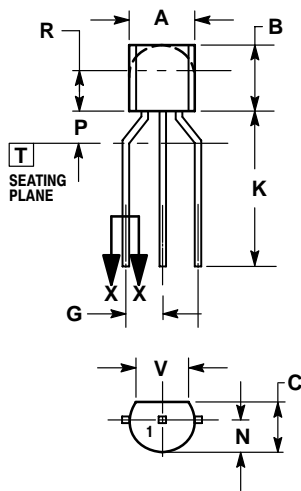
STRAIGHT LEAD
BULK PACK



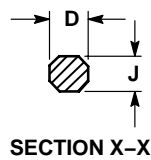
NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED.
4. LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.175	0.205	4.45	5.20
B	0.170	0.210	4.32	5.33
C	0.125	0.165	3.18	4.19
D	0.016	0.021	0.407	0.533
G	0.045	0.055	1.15	1.39
H	0.095	0.105	2.42	2.66
J	0.015	0.020	0.39	0.50
K	0.500	---	12.70	---
L	0.250	---	6.35	---
N	0.080	0.105	2.04	2.66
P	---	0.100	---	2.54
R	0.115	---	2.93	---
V	0.135	---	3.43	---



BENT LEAD
TAPE & REEL
AMMO PACK



NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED.
4. LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

DIM	MILLIMETERS	
	MIN	MAX
A	4.45	5.20
B	4.32	5.33
C	3.18	4.19
D	0.40	0.54
G	2.40	2.80
J	0.39	0.50
K	12.70	---
N	2.04	2.66
P	1.50	4.00
R	2.93	---
V	3.43	---

STYLE 1:

1. EMITTER
2. BASE
3. COLLECTOR